

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2467

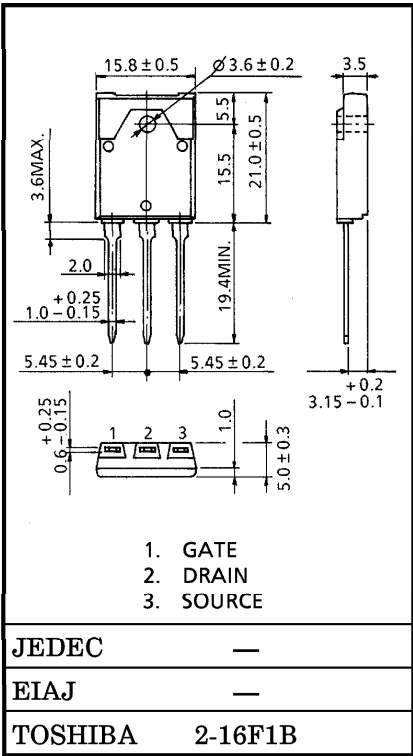
HIGH POWER AMPLIFIER APPLICATION

Unit in mm

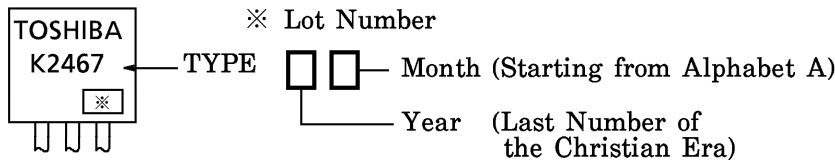
- High Breakdown Voltage : $V_{DSS} = 180\text{ V}$
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0\text{ S (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	9	A
Drain Power Dissipation (Tc = 25°C)	P_D	80	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



MARKING



Weight : 5.8 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 180\text{ V}, V_{GS} = 0$	—	—	1.0	mA
Gate Leakage Current	I_{GSS}	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$	—	—	± 0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR) DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0$	180	—	—	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	—	2.5	5.0	V
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	$V_{DS} = 10\text{ V}, I_D = 0.1\text{ A}$	1.4	—	2.8	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 3\text{ A}$	—	4.0	—	S
Input Capacitance	C_{iss}	$V_{DS} = 30\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	700	—	pF
Output Capacitance	C_{oss}	$V_{DS} = 30\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	150	—	pF
Reverse Capacitance	C_{rss}	$V_{DS} = 30\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	90	—	pF

(Note) : $V_{GS(OFF)}$ Classification Y : 1.4~2.8

**This transistor is an electrostatic sensitive device.
Please handle with caution.**